

(12) INTERNATIONAL APPLICATION PUBLISHED UNDER THE PATENT COOPERATION TREATY (PCT)

(19) World Intellectual Property Organization
International Bureau



(43) International Publication Date
31 July 2003 (31.07.2003)

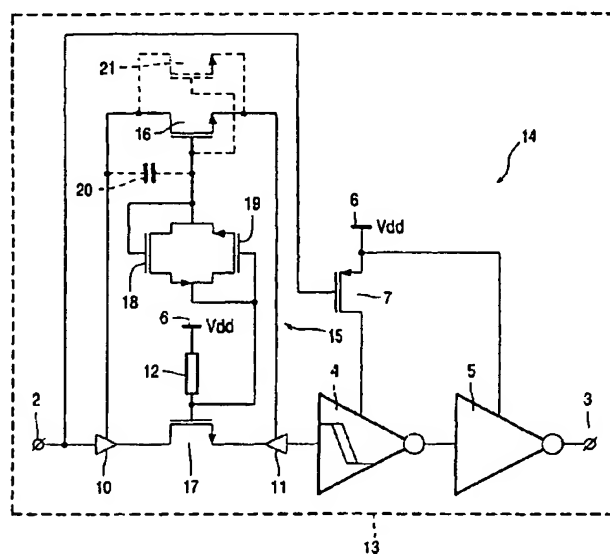
PCT

(10) International Publication Number
WO 03/063198 A2

- (51) International Patent Classification⁷: H01L (74) Agent: DULJVESTIJN, Adrianus, J.; Internationaal Octrooibureau B.V., Prof. Holstlaan 6, NL-5656 AA Eindhoven (NL).
- (21) International Application Number: PCT/IB02/05484
- (22) International Filing Date: 12 December 2002 (12.12.2002) (81) Designated States (national): AE, AG, AL, AM, AT, AU, AZ, BA, BB, BG, BR, BY, BZ, CA, CH, CN, CO, CR, CU, CZ, DE, DK, DM, DZ, EC, EE, ES, FI, GB, GD, GE, GH, GM, HR, HU, ID, IL, IN, IS, JP, KE, KG, KP, KR, KZ, LC, LK, LR, LS, LT, LU, LV, MA, MD, MG, MK, MN, MW, MX, MZ, NO, NZ, OM, PH, PL, PT, RO, RU, SC, SD, SE, SG, SK, SL, TJ, TM, TN, TR, TT, TZ, UA, UG, US, UZ, VC, VN, YU, ZA, ZM, ZW.
- (25) Filing Language: English
- (26) Publication Language: English
- (30) Priority Data: 02075258.0 22 January 2002 (22.01.2002) EP (71) Applicant (for all designated States except US): KONINKLIJKE PHILIPS ELECTRONICS N.V. [NL/NL]; Groenewoudseweg 1, NL-5621 BA Eindhoven (NL).
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(54) Title: A VOLTAGE LIMITING SEMICONDUCTOR PASS GATE CIRCUIT



(57) Abstract: A voltage limiting semiconductor pass gate circuit (15), comprises a first transistor (16), operatively connected to an input node (10) and an output node (11) of the pass gate circuit (15), and a second transistor (17), operatively connected between the input node (10) and the output node (11). The second transistor (17) has a control electrode biased to a supply voltage (6), and the first transistor (16) has a control electrode which connects by two back-to-back connected diode elements (18, 19) to the control electrode of the second transistor (17). The pass gate circuit (15) is typically applied in input I/O cells (14) of semiconductor integrated circuits (13).